Amendments to the Specification

At page 4, make the following changes to the paragraph that begins on line 9 and ends at line 16:

The HF used in etching the silicon wafers is preferably in a concentration of 0.5 to 5% by weight HF in water. The dilute HF (DHF) is preferably a solution of 0.05 to 0.25% by weight HF in water. The dilute SC1 is preferably a solution 1 part ammonium hydroxide (28% by weight) and 2 parts by weight hydrogen peroxide (30% by weight) in 50 to 200 parts water. The ozonated water in the rinse of step (B) preferably comprises less than about 10 parts per million (ppm) ozone in water. The dissolved oxygen (DO2) is preferably controlled at less than 1 part per billion (ppb) in water. The total organic carbon (TOC) is preferably less than about 1 ppb in water. The total dissolved silica is preferably less than about 1 ppb in water.

In the paragraph that bridges from page 4, line 19 to page 5, line 10, make the following changes:

FIG. 1 is a particle signature for an in situ HF last process at 0.12 μm according to the prior art.

FIG. 2 is a particle signature for an in situ HF-last process at 0.12 μm according to the invention.

FIG. 3 is a chemical flow diagram of the chemical mixing and metering system of the present invention.

FIG. 4 is a flow chart of a comparative procedure.

FIG. 5 is a flow chart of a procedure according to the invention.

FIG. 6 is a list of the parameters used in a preferred embodiment according to the invention.

FIG. 7 a table which compares different cleaning methods and compares them to the invention method.

FIG. 8 is a control particle count diagram.

FIG. 9 is a particle count diagram of a comparative process.

~~FIG. 10 is a particle count diagram of a process according to the invention.~~

~~FIG. 6 is a particle count diagram of a process according to the invention.~~

~~FIG. 7 is a particle count diagram of a process according to the invention.~~

~~FIG. 8 is a particle count diagram of a control.~~

~~FIG. 9 is a particle count diagram of a comparative method.~~

FIG. 10 is a particle count diagram of a process according to the invention.

FIG. 11 is a particle count diagram of according to a comparative process.

FIG. 12 is a particle count diagram of a process according to the invention.

FIG. 13 is a particle count diagram of a process according to the invention

FIG. 14 is a particle count diagram after step B of the invention

FIG. 15 is a particle count of a method of the invention.

FIG. 16 is a table of data demonstrating etch and ER uniformity according to the invention.

FIG. 17 is a diagram showing defects according to the method of the invention.